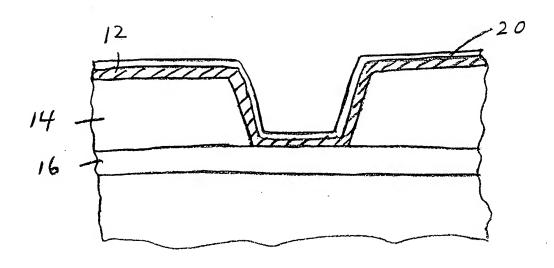
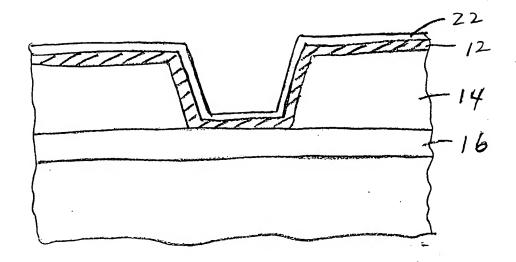


FIG. 1A



F1G. 1B



F14. 1C

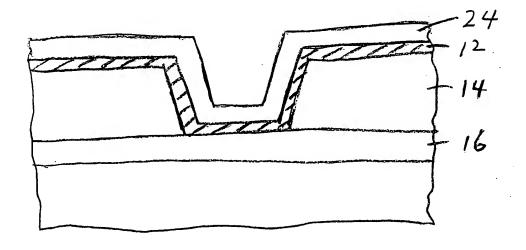
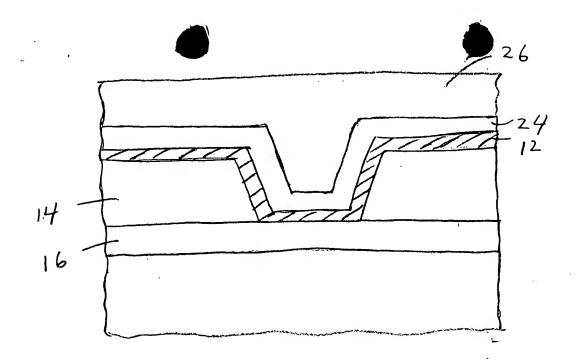


FIG. 10



F14. 1E



DEPOSIT TIN BARRIER LAYER ON SEMICONDUCTOR DEVICE SUBSTRATE FORM LAYER OF SILICON ON TIN BARRIER LAYER EXPOSE LAYER DF SILICON TO WF6 TO FORM TUNGSTEN LAYER CONDUCT ALTERNATING EXPOSURE OF TUNGSTEN LAYER TO SiH4 AND WF6 DEPOSIT TUNGSTEN 58 CORE LAYER FIG. 2